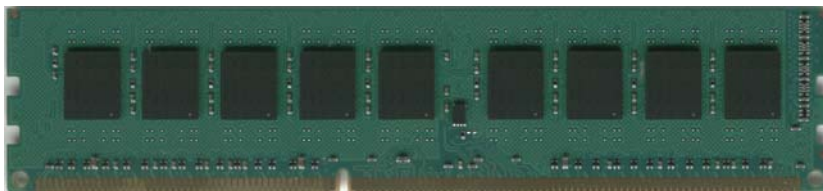


DTM64396C

8 GB - 240-Pin 2Rx8 Unbuffered ECC DDR3 DIMM



Identification

DTM64396C 1Gx72
8GB 2Rx8 PC3-12800E-11-11-E2

Performance range

Clock / Module Speed / CL-t_{RCD} -t_{RP}

800 MHz / PC3-12800 / 11-11-11
667 MHz / PC3-10600 / 10-10-10
667 MHz / PC3-10600 / 9-9-9
533 MHz / PC3-8500 / 8-8-8
533 MHz / PC3-8500 / 7-7-7
400 MHz / PC3-6400 / 6-6-6

Features

240-pin JEDEC-compliant DIMM, 133.35 mm wide by 30 mm high
Operating Voltage: 1.5 V ±0.075 V, I/O Type: SSTL_15
On-board I ² C temperature sensor with integrated Serial Presence-Detect (SPD) EEPROM
Data Transfer Rate: 12.8 Gigabytes/sec
Data Bursts: 8 and burst chop 4 mode
ZQ Calibration for Output Driver and On-Die Termination (ODT)
Programmable ODT / Dynamic ODT during Writes
Programmable CAS Latency: 6, 7, 8, 9, 10, and 11
Differential Data Strobe signals
SDRAM Addressing (Row/Col/Bank): 16/10/3
Fully RoHS Compliant

Description

DTM64396C is an Unbuffered 1Gx72 memory module, which conforms to JEDEC's DDR3, PC3-12800 standard. The assembly is Dual-Rank. Each Rank is comprised of nine 512Mx8 DDR3-1600 Hynix SDRAMs. One 2K-bit EEPROM is used for Serial Presence Detect.

A thermal sensor accurately monitors the DIMM module and can prevent exceeding the maximum operating temperature of 95C.

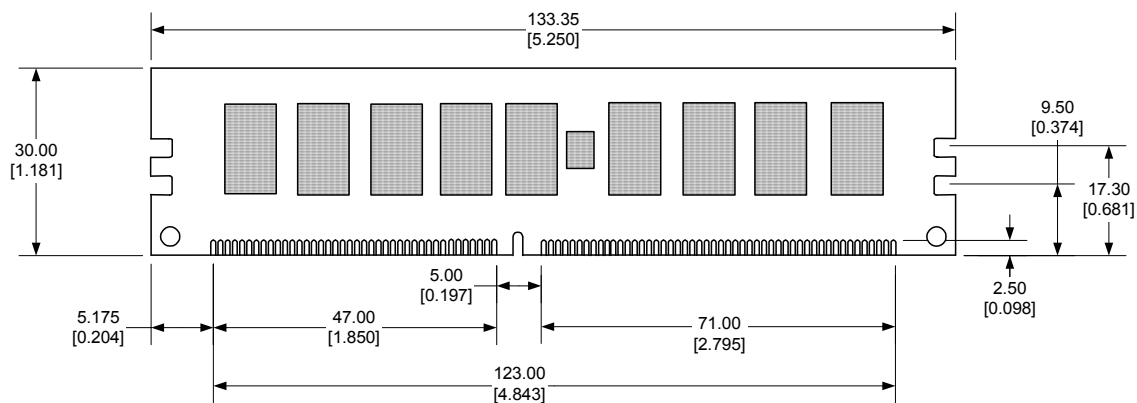
Both output driver strength and input termination impedance are programmable to maintain signal integrity on the I/O signals.

Pin Configuration

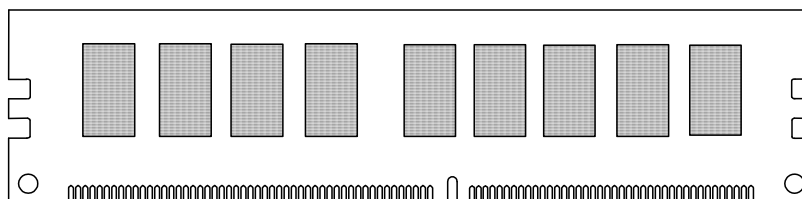
Front Side				Back Side				Name	Function
1 V _{REFDQ}	31 DQ25	61 A2	91 DQ41	121 V _{SS}	151 V _{SS}	181 A1	211 V _{SS}	CB[7:0]	Data Check Bits
2 V _{SS}	32 V _{SS}	62 V _{DD}	92 V _{SS}	122 DQ4	152 DM3	182 V _{DD}	212 DM5	DQ[63:0]	Data Bits
3 DQ0	33 /DQS3	63 CK1	93 /DQS5	123 DQ5	153 NC	183 V _{DD}	213 NC	DQS[8:0], /DQS[8:0]	Differential Data Strobes
4 DQ1	34 DQS3	64 /CK1	94 DQS5	124 V _{SS}	154 V _{SS}	184 CK0	214 V _{SS}	DM[8:0]	Data Mask
5 V _{SS}	35 V _{SS}	65 V _{DD}	95 V _{SS}	125 DM0	155 DQ30	185 /CK0	215 DQ46	CK[1:0], /CK[1:0]	Differential Clock Inputs
6 /DQS0	36 DQ26	66 V _{DD}	96 DQ42	126 NC	156 DQ31	186 V _{DD}	216 DQ47	CKE[1:0]	Clock Enables
7 DQS0	37 DQ27	67 V _{REFCA}	97 DQ43	127 V _{SS}	157 V _{SS}	187 /Event	217 V _{SS}	/CAS	Column Address Strobe
8 V _{SS}	38 V _{SS}	68 P _{ARL} _IN, NC*	98 V _{SS}	128 DQ6	158 CB4	188 A0	218 DQ52	/RAS	Row Address Strobe
9 DQ2	39 CB0	69 VDD	99 DQ48	129 DQ7	159 CB5	189 V _{DD}	219 DQ53	/S[3:0]	Chip Selects
10 DQ3	40 CB1	70 A10/AP	100 DQ49	130 V _{SS}	160 V _{SS}	190 BA1	220 V _{SS}	/WE	Write Enable
11 V _{SS}	41 V _{SS}	71 BA0	101 V _{SS}	131 DQ12	161 DM8	191 V _{DD}	221 DM6	A[15:0]	Address Inputs
12 DQ8	42 /DQS8	72 V _{DD}	102 /DQS6	132 DQ13	162 NC	192 /RAS	222 NC	BA[2:0]	Bank Addresses
13 DQ9	43 DQS8	73 /WE	103 DQS6	133 V _{SS}	163 V _{SS}	193 /S0	223 V _{SS}	ODT[1:0]	On Die Termination Inputs
14 V _{SS}	44 V _{SS}	74 /CAS	104 V _{SS}	134 DM1	164 CB6	194 V _{DD}	224 DQ54	SA[2:0]	SPD Address
15 /DQS1	45 CB2	75 V _{DD}	105 DQ50	135 NC	165 CB7	195 ODT0	225 DQ55	SCL	SPD Clock Input
16 DQS1	46 CB3	76 /S1	106 DQ51	136 V _{SS}	166 V _{SS}	196 A13	226 V _{SS}	SDA	SPD Data Input/Output
17 V _{SS}	47 V _{SS}	77 ODT1	107 V _{SS}	137 DQ14	167 NC (TEST)	197 V _{DD}	227 DQ60	/EVENT	Temperature Sensing
18 DQ10	48 V _{TT} , NC	78 V _{DD}	108 DQ56	138 DQ15	168 /RESET	198 /S3, NC*	228 DQ61	/RESET	Reset for register and DRAMs
19 DQ11	49 V _{TT} , NC	79 /S2, NC	109 DQ57	139 V _{SS}	169 CKE1	199 V _{SS}	229 V _{SS}	PAR_IN	Parity bit for Addr/Ctrl
20 V _{SS}	50 CKE0	80 V _{SS}	110 V _{SS}	140 DQ20	170 V _{DD}	200 DQ36	230 DM7	/ERR_OUT	Error bit for Parity Error
21 DQ16	51 V _{DD}	81 DQ32	111 /DQS7	141 DQ21	171 A15	201 DQ37	231 NC	A12/BC	Combination input: Addr12/Burst Chop
22 DQ17	52 BA2	82 DQ33	112 DQS7	142 V _{SS}	172 A14	202 V _{SS}	232 V _{SS}	A10/AP	Combination input: Addr10/Auto-precharge
23 V _{SS}	53 /ERR_OUT, NC*	83 V _{SS}	113 V _{SS}	143 DM2	173 V _{DD}	203 DM4	233 DQ62	V _{SS}	Ground
24 /DQS2	54 V _{DD}	84 /DQS4	114 DQ58	144 NC	174 A12/BC	204 NC	234 DQ63	V _{DD}	Power
25 DQS2	55 A11	85 DQS4	115 DQ59	145 V _{SS}	175 A9	205 V _{SS}	235 V _{SS}	V _{DDSPD}	SPD EEPROM Power
26 V _{SS}	56 A7	86 V _{SS}	116 V _{SS}	146 DQ22	176 V _{DD}	206 DQ38	236 V _{DDSPD}	V _{REFDQ}	Reference Voltage for DQ's
27 DQ18	57 V _{DD}	87 DQ34	117 SA0	147 DQ23	177 A8	207 DQ39	237 SA1	V _{REFCA}	Reference Voltage for CA
28 DQ19	58 A5	88 DQ35	118 SCL	148 V _{SS}	178 A6	208 V _{SS}	238 SDA	V _{TT}	Termination Voltage
29 V _{SS}	59 A4	89 V _{SS}	119 SA2	149 DQ28	179 V _{DD}	209 DQ44	239 V _{SS}	NC	No Connection
30 DQ24	60 V _{DD}	90 DQ40	120 V _{TT}	150 DQ29	180 A3	210 DQ45	240 V _{TT}		

* - Not used

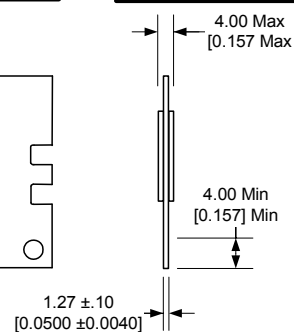
Front view



Back view



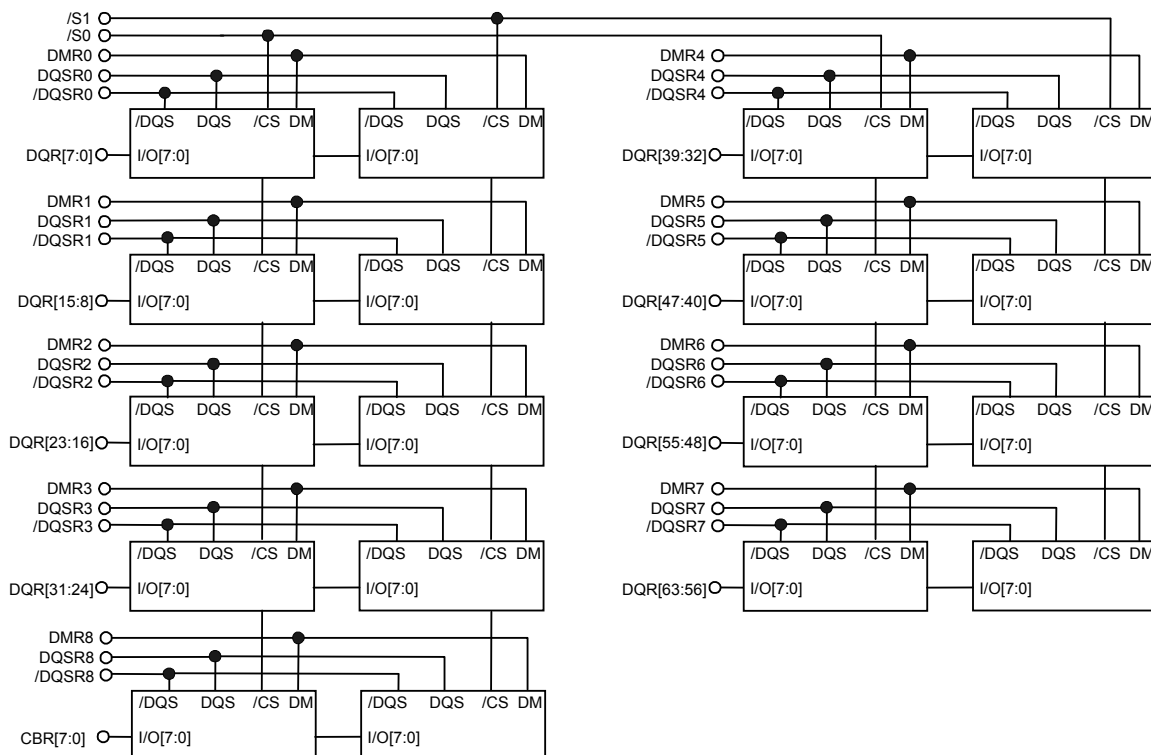
Side view



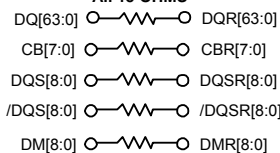
Notes

Tolerances on all dimensions except where otherwise indicated are $\pm .13$ (.005).

All dimensions are expressed: millimeters [inches]

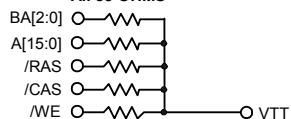


All 15 OHMS

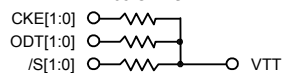


GLOBAL SDRAM CONNECTS

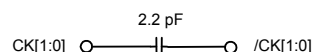
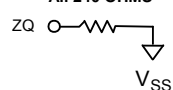
All 39 OHMS



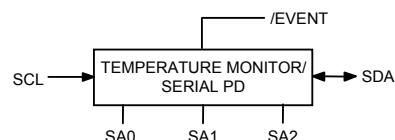
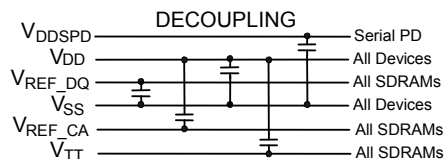
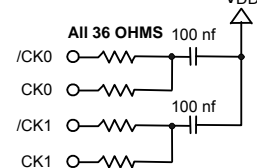
All 39 OHMS



All 240 OHMS



All 36 OHMS



Absolute Maximum Ratings

(Note: Operation at or above Absolute Maximum Ratings can adversely affect module reliability.)

PARAMETER	Symbol	Minimum	Maximum	Unit
Temperature, non-Operating	$T_{STORAGE}$	-55	100	C
Ambient Temperature, Operating	T_A	0	70	C
DRAM Case Temperature, Operating	T_{CASE}	0	95	C
Voltage on V_{DD} relative to V_{SS}	V_{DD}	-0.4	1.975	V
Voltage on Any Pin relative to V_{SS}	V_{IN}, V_{OUT}	-0.4	1.975	V

Notes:

DRAM Operating Case Temperature above 85C requires 2X refresh.

Recommended DC Operating Conditions ($T_A = 0$ to 70 C, Voltage referenced to $V_{SS} = 0$ V)

PARAMETER	Symbol	Minimum	Typical	Maximum	Unit	Note
Power Supply Voltage	V_{DD}	1.425	1.5	1.575	V	
I/O Reference Voltage	V_{REFDQ}	0.49 V_{DD}	0.50 V_{DD}	0.51 V_{DD}	V	1
I/O Reference Voltage	V_{REFCA}	0.49 V_{DD}	0.50 V_{DD}	0.51 V_{DD}	V	1

Notes:

The value of V_{REF} is expected to equal one-half V_{DD} and to track variations in the V_{DD} DC level. Peak-to-peak noise on V_{REF} may not exceed $\pm 1\%$ of its DC value. For Reference $V_{DD}/2 \pm 15$ mV.

DC Input Logic Levels, Single-Ended ($T_A = 0$ to 70 C, Voltage referenced to $V_{SS} = 0$ V)

PARAMETER	Symbol	Minimum	Maximum	Unit
Logical High (Logic 1)	$V_{IH(DC)}$	$V_{REF} + 0.1$	V_{DD}	V
Logical Low (Logic 0)	$V_{IL(DC)}$	V_{SS}	$V_{REF} - 0.1$	V

AC Input Logic Levels, Single-Ended ($T_A = 0$ to 70 C, Voltage referenced to $V_{SS} = 0$ V)

PARAMETER	Symbol	Minimum	Maximum	Unit
Logical High (Logic 1)	$V_{IH(AC)}$	$V_{REF} + 0.175$	-	V
Logical Low (Logic 0)	$V_{IL(AC)}$	-	$V_{REF} - 0.175$	V

Differential Input Logic Levels ($T_A = 0$ to 70°C , Voltage referenced to $V_{SS} = 0\text{ V}$)

PARAMETER	Symbol	Minimum	Maximum	Unit
Differential Input Logic High	$V_{IH,DIFF}$	+0.200	DC: V_{DD} AC: $V_{DD}+0.4$	V
Differential Input Logic Low	$V_{IL,DIFF}$	DC: V_{SS} AC: $V_{SS}-0.4$	-0.200	V
Differential Input Cross Point Voltage relative to $V_{DD}/2$	V_{IX}	- 0.150	+ 0.150	V

Capacitance ($T_A = 25^\circ\text{C}$, $f = 100\text{ MHz}$)

PARAMETER	Pin	Symbol	Minimum	Maximum	Unit
Input Capacitance, Clock	CK0, /CK0, CK1, /CK1	C_{CK}	7.2	13.5	pF
Input Capacitance, Address	BA[2:0], A[15:0], /RAS, /CAS, /WE	C_I	13.5	27	pF
Input Capacitance Control	/S0, /S1, CKE0, CKE1, ODT0, ODT1	C_I	6.8	13.5	pF
Input/Output Capacitance	DQ[63:0], CB[7:0] DQS[8:0], /DQS[8:0], DM[8:0]	C_{IO}	3	5	pF

DC Characteristics ($T_A = 0$ to 70°C , Voltage referenced to $V_{SS} = 0\text{ V}$)

PARAMETER	Symbol	Minimum	Maximum	Unit	Note
Input Leakage Current (Any input $0\text{ V} < V_{IN} < V_{DD}$)	I_{IL}	-18	+18	μA	1,2
Output Leakage Current ($0\text{ V} < V_{OUT} < V_{DDQ}$)	I_{OL}	-10	+10	μA	2,3

Notes:

- 1) All other pins not under test = 0 V
- 2) Values are shown per pin
- 3) DQ's, DQS, DQS and ODT are disabled

I_{DD} Specifications and Conditions (T_A = 0 to 70 °C, Voltage referenced to V_{SS} = 0 V)

PARAMETER	Symbol	Test Condition	Max Value	Unit
Operating One Bank Active-Precharge Current	I _{DD0} *	Operating current : One bank ACTIVATE-to-PRECHARGE	765	mA
Operating One Bank Active-Read-Precharge Current	I _{DD1} *	Operating current : One bank ACTIVATE-to-READ-to-PRECHARGE	855	mA
Precharge Power-Down Current	I _{DD2P} **	Precharge power down current: (Slow exit)	360	mA
Precharge Power-Down Current	I _{DD2P} **	Precharge power down current: (Fast exit)	369	mA
Precharge Quiet Standby Current	I _{DD2Q} **	Precharge quiet standby current	540	mA
Precharge Standby Current	I _{DD2N} **	Precharge standby current	540	mA
Active Power-Down Current	I _{DD3P} **	Active power-down current	450	mA
Active Standby Current	I _{DD3N} **	Active standby current	630	mA
Operating Burst Write Current	I _{DD4W} *	Burst write operating current	1485	mA
Operating Burst Read Current	I _{DD4R} *	Burst read operating current	1440	mA
Burst Refresh Current	I _{DD5} **	Refresh current	1620	mA
Self Refresh Current	I _{DD6} **	Self-refresh temperature current: MAX T _c = 85°C	360	mA
Operating Bank Interleave Read Current	I _{DD7} **	All bank interleaved read current	1935	mA

* One module rank in this operation rest in IDD2P slow exit.

** All module ranks in this operation.

Subject to change

AC Operating Conditions

PARAMETER	Symbol	Min	Max	Unit
Internal read command to first data	t_{AA}	13.125	20	ns
CAS-to-CAS Command Delay	t_{CCD}	4	-	t_{CK}
Clock High Level Width	$t_{CH(avg)}$	0.47	0.53	t_{CK}
Clock Cycle Time	t_{CK}	1.25	1.875	ns
Clock Low Level Width	$t_{CL(avg)}$	0.47	0.53	t_{CK}
Data Input Hold Time after DQS Strobe	t_{DH}	45	-	ps
DQ Input Pulse Width	t_{DIPW}	360	-	ps
DQS Output Access Time from Clock	t_{DQSCK}	-225	+225	ps
Write DQS High Level Width	t_{DQSH}	0.45	0.55	$t_{CK(avg)}$
Write DQS Low Level Width	t_{DQSL}	0.45	0.55	$t_{CK(avg)}$
DQS-Out Edge to Data-Out Edge Skew	t_{DQSQ}	-	100	ps
Data Input Setup Time Before DQS Strobe	t_{DS}	10	-	ps
DQS Falling Edge from Clock, Hold Time	t_{DSH}	0.2	-	$t_{CK(avg)}$
DQS Falling Edge to Clock, Setup Time	t_{DSS}	0.2	-	$t_{CK(avg)}$
Clock Half Period	t_{HP}	minimum of t_{CH} or t_{CL}	-	ns
Address and Command Hold Time after Clock	t_{IH}	120	-	ps
Address and Command Setup Time before Clock	t_{IS}	45	-	ps
Load Mode Command Cycle Time	t_{MRD}	4	-	t_{CK}
DQ-to-DQS Hold	t_{QH}	0.38	-	$t_{CK(avg)}$
Active-to-Precharge Time	t_{RAS}	35	$9 \cdot t_{REFI}$	ns
Active-to-Active / Auto Refresh Time	t_{RC}	48.125	-	ns
RAS-to-CAS Delay	t_{RCD}	13.125	-	ns
Average Periodic Refresh Interval $0^{\circ}C \leq T_{CASE} < 85^{\circ}C$	t_{REFI}	-	7.8	μs
Average Periodic Refresh Interval $0^{\circ}C \leq T_{CASE} < 95^{\circ}C$	t_{REFI}	-	3.9	μs
Auto Refresh Row Cycle Time	t_{RFC}	260	-	ns
Row Precharge Time	t_{RP}	13.125	-	ns
Read DQS Preamble Time	t_{RPRE}	0.9	Note-1	$t_{CK(avg)}$
Read DQS Postamble Time	t_{RPST}	0.3	Note-2	$t_{CK(avg)}$
Row Active to Row Active Delay	t_{RRD}	Max(4nCK, 6ns)	-	ns
Internal Read to Precharge Command Delay	t_{RTP}	Max(4nCK, 7.5ns)	-	ns
Write DQS Preamble Setup Time	t_{WPRE}	0.9	-	$t_{CK(avg)}$
Write DQS Postamble Time	t_{WPST}	0.3	-	$t_{CK(avg)}$
Write Recovery Time	t_{WR}	15	-	ns
Internal Write to Read Command Delay	t_{WTR}	Max(4nCK, 7.5ns)	-	ns

Notes:

1. The maximum preamble is bound by $t_{LZDQS(min)}$
2. The maximum postamble is bound by $t_{HZDQS(max)}$



DTM64396C

8 GB - 240-Pin 2Rx8 Unbuffered ECC DDR3 DIMM



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